

## H7N1004DL, H7N1004DS

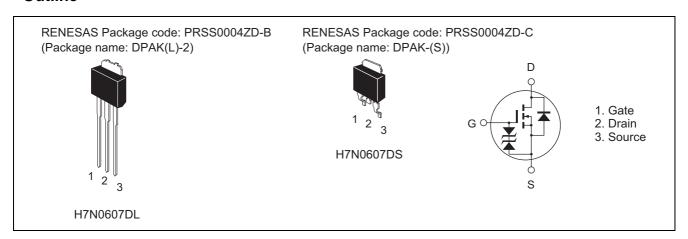
# Silicon N-Channel MOSFET High-Speed Power Switching

REJ03G1482-0100 Rev.1.00 Nov 07, 2006

#### **Features**

- Low on-resistance  $R_{DS(on)} = 25 \text{ m}\Omega \text{ typ.}$
- Low drive current
- Available for 4.5 V gate drive

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit
Drain to source voltage	$V_{DSS}$	100	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	I <sub>D</sub>	25	Α
Drain peak current	I <sub>D</sub> (pulse) <sup>Note1</sup>	75	А
Body-drain diode reverse drain current	I <sub>DR</sub>	75	А
Avalanche current	I <sub>AP</sub> Note 3	15	Α
Avalanche energy	E <sub>AR</sub> Note 3	22.5	mJ
Channel dissipation	Pch Note 2	30	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$

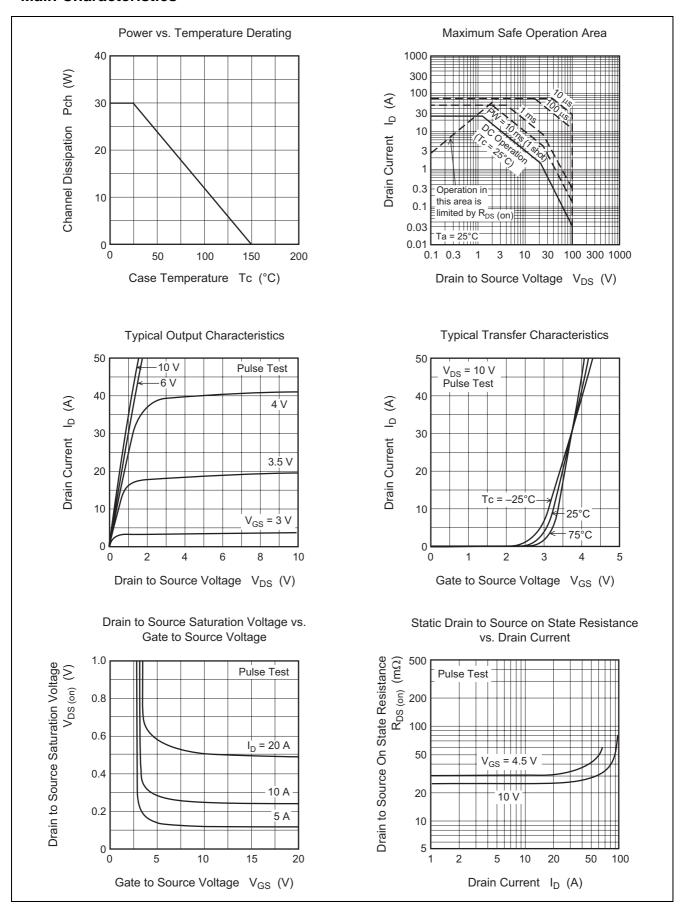
#### **Electrical Characteristics**

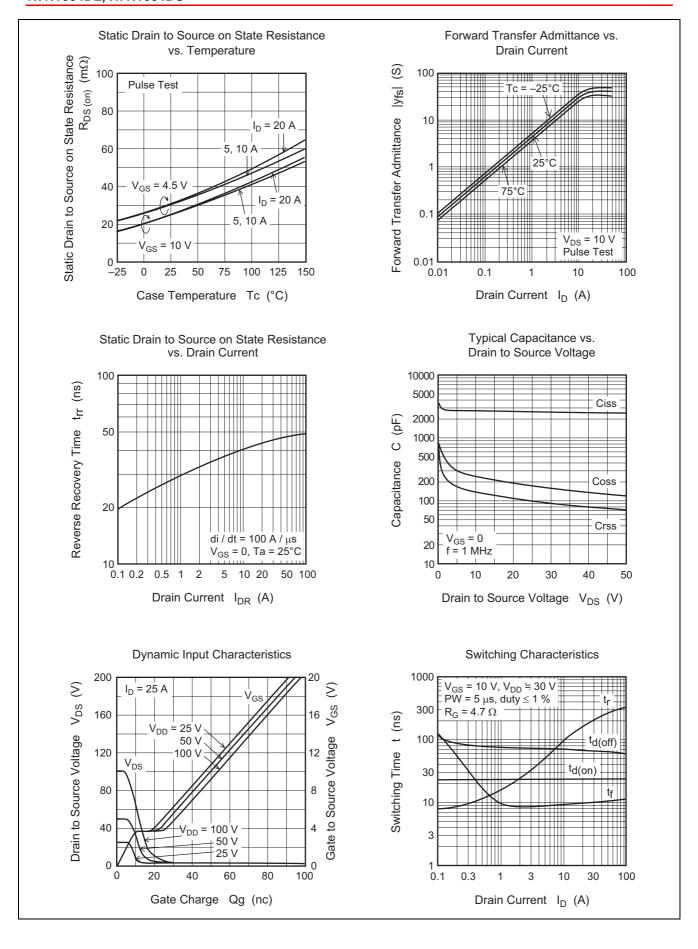
 $(Ta = 25^{\circ}C)$ 

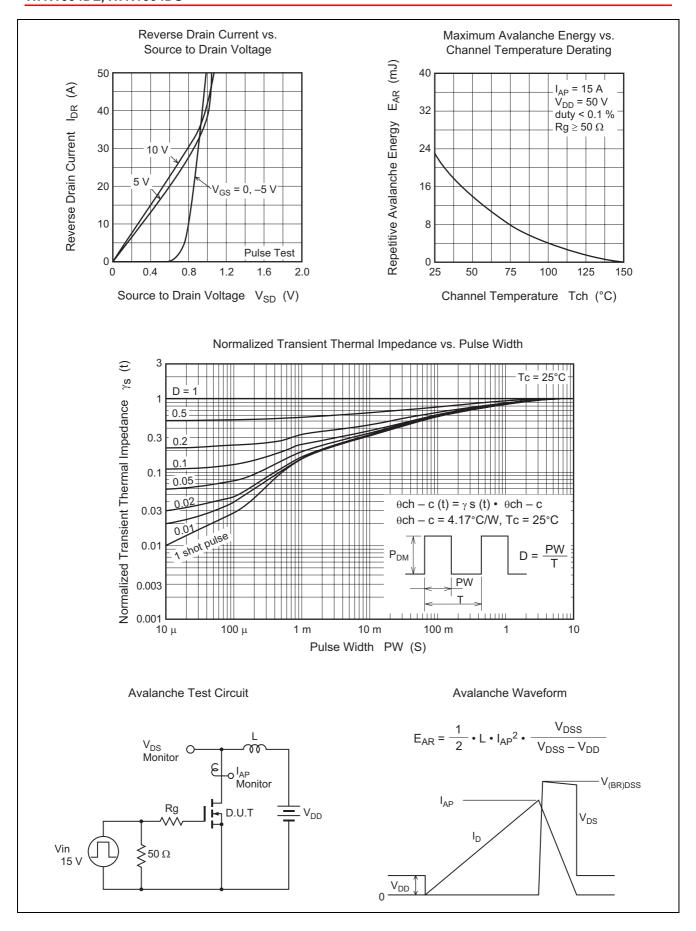
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	10	μΑ	$V_{DS} = 100 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	_	2.5	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note 4}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	25	35	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 4}}$
resistance		_	30	45	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note 4}}$
Forward transfer admittance	y <sub>fs</sub>	20	35	_	S	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 4}}$
Input capacitance	Ciss	_	2800	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	240	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	140	_	pF	f = 1 MHz
Total gate charge	Qg	_	50	_	nC	V <sub>DD</sub> = 50 V
Gate to source charge	Qgs	_	9	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	11	_	nC	I <sub>D</sub> = 25 A
Turn-on delay time	t <sub>d(on)</sub>	_	23	_	ns	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12.5 A
Rise time	t <sub>r</sub>	_	110	_	ns	$R_L = 2.4 \Omega$
Turn-off delay time	t <sub>d(off)</sub>	_	70	_	ns	$Rg = 4.7 \Omega$
Fall time	t <sub>f</sub>	_	9.5	_	ns	1
Body-drain diode forward voltage	$V_{DF}$	_	0.89	_	V	I <sub>F</sub> = 25 A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	45	_	ns	$I_F = 25 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

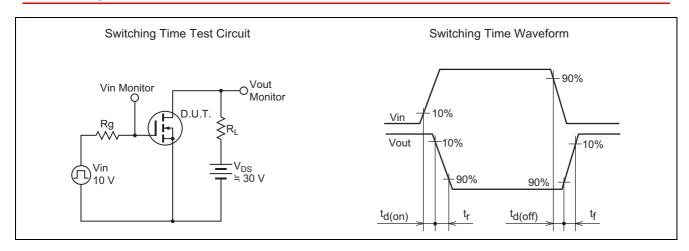
Notes: 4. Pulse test

#### **Main Characteristics**



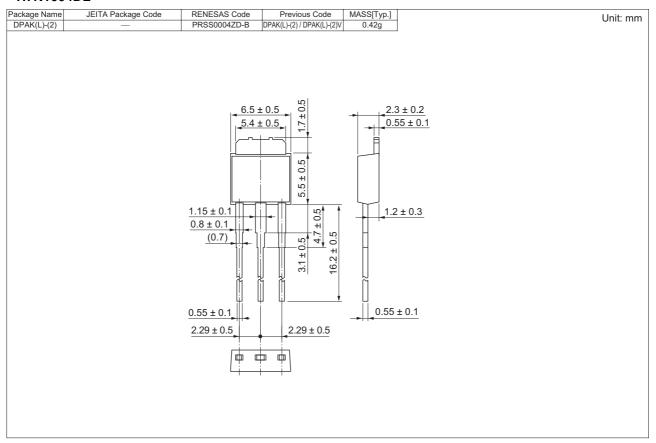




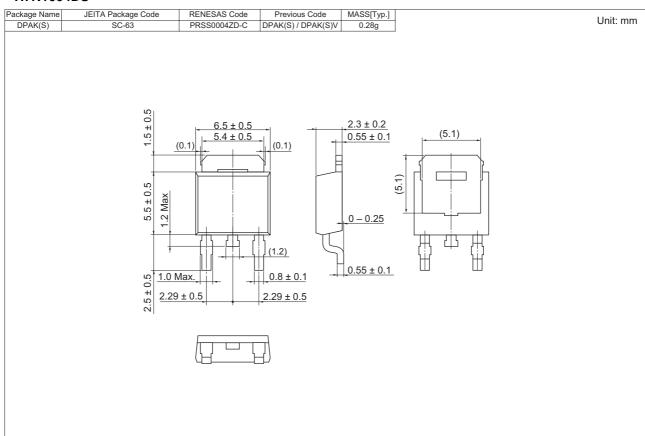


#### **Package Dimensions**

#### • H7N1004DL



#### • H7N1004DS



## **Ordering Information**

Part Name	Quantity	Shipping Container
H7N1004DL	100 pcs	Sack
H7N1004DSTL	3000 pcs	Taping
H7N1004DL-E	100 pcs	Sack
H7N1004DSTL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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